

EAST - [jig.wsp:1]

Ble View Edit Tools Window Help

Drafts Pending Active Failed

L1: (1634) STI.clm. or (shallow adj trench adj isolation).clm.
 L2: (83) 1 and (second adj (mask or resist or photoresist)).clm.
 L3: (70) 2 and (etch\$3.clm. or pattern\$3.clm.)
 L4: (26) 3 and (etch\$3 near (mask or photoresist or resist))
 L5: (9) 3 and (remov\$3 near (second adj mask))

USPAT-US-POPUP

Default operator: OR

3 and (remov\$3 near (second adj mask))

Assum. Diff. Item. Change Test. Form

U	I	Document ID	Issue Date	Pages	Title	Current OR	Current ERef	Retrieval C	Inventor	S	C	P	X	Y	Z	Image	
1	<input type="checkbox"/>	US 20040005752	20040108	19	voltage threshold and low A1	438/217			Heim, Mark et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 2004	
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20030124013	20030703	9	Method of fabricating shallow trench isolation A1	438/400	257/E21.232;		Lee, Shyh-Dar	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 2003				
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20030119248	20030626	13	Method of fabricating dual threshold voltage n-channel A1	438/217	257/E21.633;		Mistry, Kaizad R. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 2003				
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20030094659	20030522	13	METHOD OF FABRICATING DUAL THRESHOLD VOLTAGE N-CHANNEL A1	257/369	438/289;		MISTRY, KAIZAD R. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 2003				
5	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 20020016035	20020207	17	Method for making deep trench capacitors for DRAMs A1	438/243	438/386		Wu, Chao-Chueh et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 2002				
6	<input type="checkbox"/>	<input type="checkbox"/>	US 6475894 B1	20021105	18	Process for fabricating a floating gate of a flash memory A1	438/593	257/E21.209;		Huang, Chung-Lin et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6				
7	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6323092 B1	20011127	8	Method for forming a shallow trench isolation A1	438/296	257/E21.548;		Lee, Hao-Ming	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6				
8	<input type="checkbox"/>	<input type="checkbox"/>	US 6281069 B1	20010828	10	Method for forming deep trench capacitor under a shallow trench isolation A1	438/248	438/404;		Wu, Der-Yuan et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6				
9	<input type="checkbox"/>	<input type="checkbox"/>	US 6245635 B1	20010612	18	Method of fabricating shallow trench isolation A1	438/407	257/E21.653;		Lee, Ellis	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6				

Ready